

# Amplifier Transistors

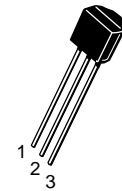
## NPN Silicon

# 2N5550 2N5551\*

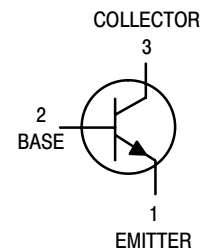
\*ON Semiconductor Preferred Device

### MAXIMUM RATINGS

Rating	Symbol	2N5550	2N5551	Unit
Collector–Emitter Voltage	$V_{CEO}$	140	160	Vdc
Collector–Base Voltage	$V_{CBO}$	160	180	Vdc
Emitter–Base Voltage	$V_{EBO}$	6.0		Vdc
Collector Current — Continuous	$I_C$	600		mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	625	5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	1.5	12	Watts mW/°C
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	–55 to +150		°C



CASE 29–11, STYLE 1  
TO–92 (TO–226AA)



### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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### OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage <sup>(1)</sup> ( $I_C = 1.0 \text{ mAdc}, I_E = 0$ )	$V_{(BR)CEO}$	140 160	—	Vdc
Collector–Base Breakdown Voltage ( $I_C = 100 \mu\text{Adc}, I_E = 0$ )	$V_{(BR)CBO}$	160 180	—	Vdc
Emitter–Base Breakdown Voltage ( $I_E = 10 \mu\text{Adc}, I_C = 0$ )	$V_{(BR)EBO}$	6.0	—	Vdc
Collector Cutoff Current ( $V_{CB} = 100 \text{ Vdc}, I_E = 0$ ) ( $V_{CB} = 120 \text{ Vdc}, I_E = 0$ ) ( $V_{CB} = 100 \text{ Vdc}, I_E = 0, T_A = 100^\circ\text{C}$ ) ( $V_{CB} = 120 \text{ Vdc}, I_E = 0, T_A = 100^\circ\text{C}$ )	$I_{CBO}$	— — — —	100 50 100 50	nAdc   $\mu\text{Adc}$
Emitter Cutoff Current ( $V_{EB} = 4.0 \text{ Vdc}, I_C = 0$ )	$I_{EBO}$	—	50	nAdc

1. Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle = 2.0%.

Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

# 2N5550 2N5551

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit	
<b>ON CHARACTERISTICS(1)</b>					
DC Current Gain (I <sub>C</sub> = 1.0 mA <sub>dc</sub> , V <sub>CE</sub> = 5.0 V <sub>dc</sub> )	h <sub>FE</sub>	2N5550 60	—	—	
2N5551 80		—			
(I <sub>C</sub> = 10 mA <sub>dc</sub> , V <sub>CE</sub> = 5.0 V <sub>dc</sub> )	h <sub>FE</sub>	2N5550 60	250	—	
2N5551 80		250			
(I <sub>C</sub> = 50 mA <sub>dc</sub> , V <sub>CE</sub> = 5.0 V <sub>dc</sub> )	h <sub>FE</sub>	2N5550 20	—	—	
2N5551 30		—			
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 10 mA <sub>dc</sub> , I <sub>B</sub> = 1.0 mA <sub>dc</sub> )	V <sub>CE(sat)</sub>	Both Types	—	0.15	V <sub>dc</sub>
(I <sub>C</sub> = 50 mA <sub>dc</sub> , I <sub>B</sub> = 5.0 mA <sub>dc</sub> )		2N5550 2N5551	— —	0.25 0.20	
Base–Emitter Saturation Voltage (I <sub>C</sub> = 10 mA <sub>dc</sub> , I <sub>B</sub> = 1.0 mA <sub>dc</sub> )	V <sub>BE(sat)</sub>	Both Types	—	1.0	V <sub>dc</sub>
(I <sub>C</sub> = 50 mA <sub>dc</sub> , I <sub>B</sub> = 5.0 mA <sub>dc</sub> )		2N5550 2N5551	— —	1.2 1.0	

## SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product (I <sub>C</sub> = 10 mA <sub>dc</sub> , V <sub>CE</sub> = 10 V <sub>dc</sub> , f = 100 MHz)	f <sub>T</sub>	100	300	MHz	
Output Capacitance (V <sub>CB</sub> = 10 V <sub>dc</sub> , I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>obo</sub>	—	6.0	pF	
Input Capacitance (V <sub>EB</sub> = 0.5 V <sub>dc</sub> , I <sub>C</sub> = 0, f = 1.0 MHz)	C <sub>ibo</sub>	2N5550	—	30	pF
2N5551		—	20		
Small–Signal Current Gain (I <sub>C</sub> = 1.0 mA <sub>dc</sub> , V <sub>CE</sub> = 10 V <sub>dc</sub> , f = 1.0 kHz)	h <sub>fe</sub>	50	200	—	
Noise Figure (I <sub>C</sub> = 250 μA <sub>dc</sub> , V <sub>CE</sub> = 5.0 V <sub>dc</sub> , R <sub>S</sub> = 1.0 kΩ, f = 1.0 kHz)	NF	—	10	dB	
2N5551	—	8.0			

1. Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.

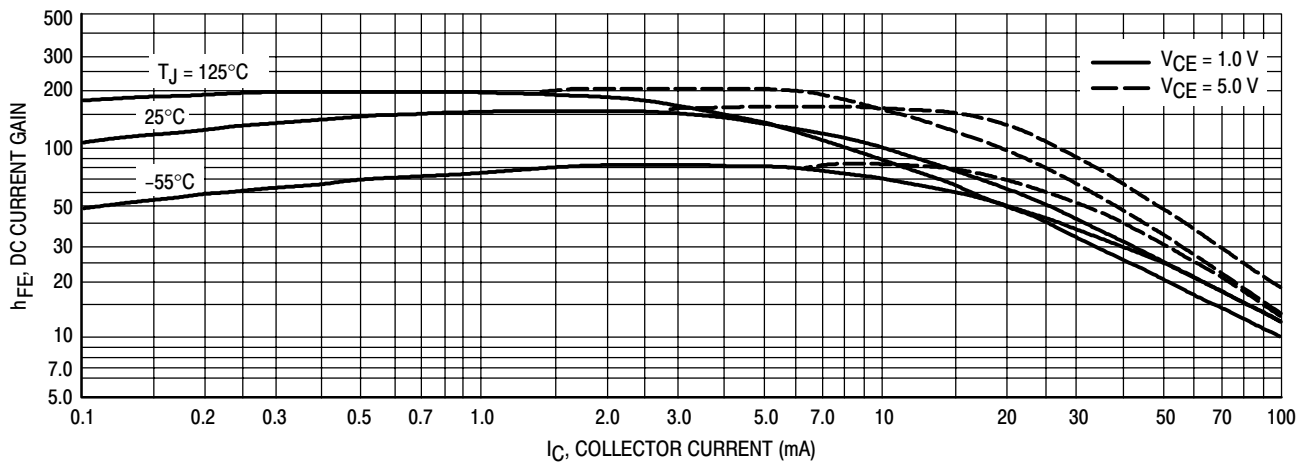


Figure 1. DC Current Gain

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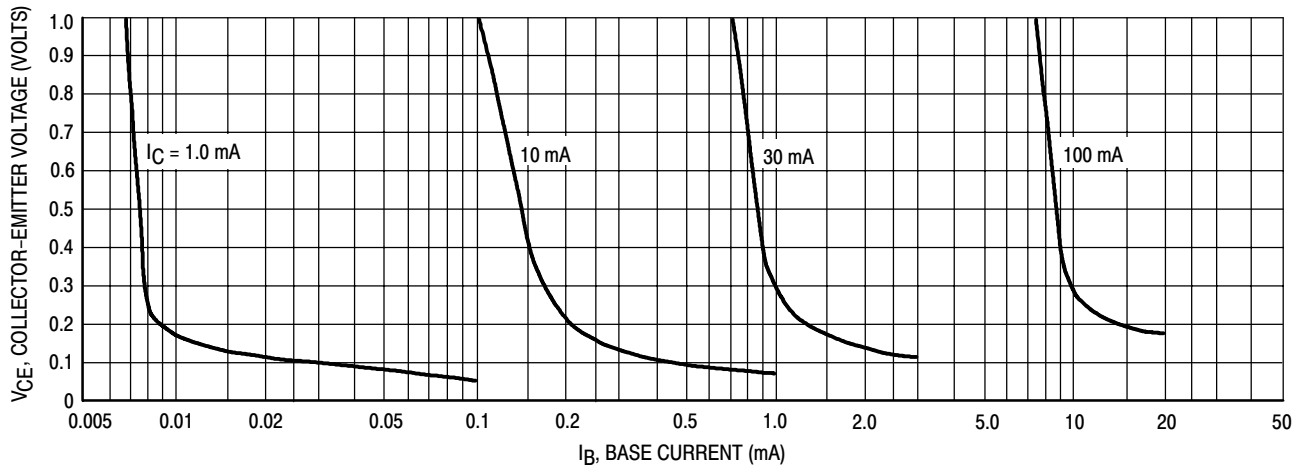


Figure 2. Collector Saturation Region

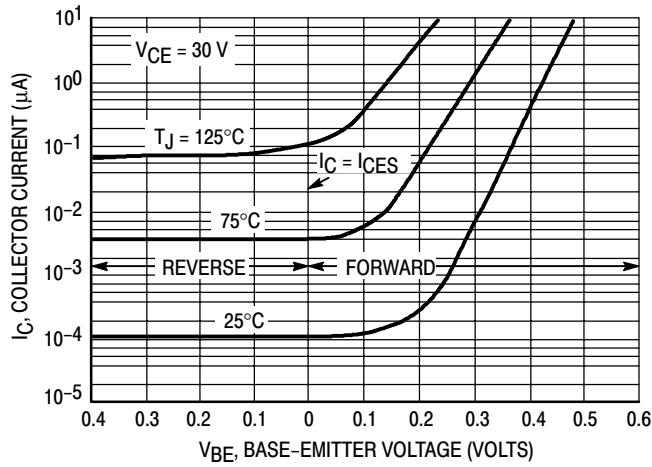


Figure 3. Collector Cut-Off Region

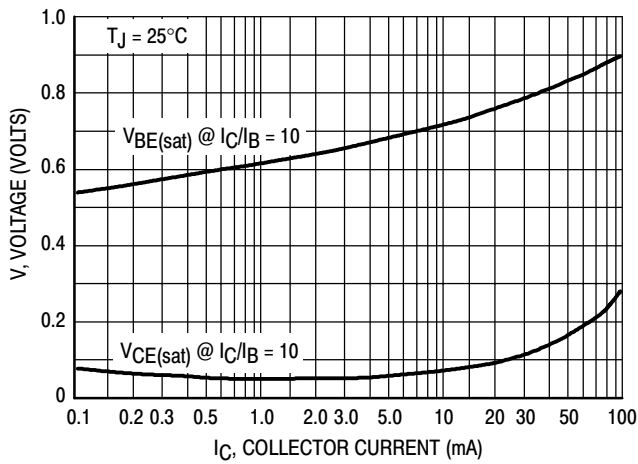


Figure 4. "On" Voltages

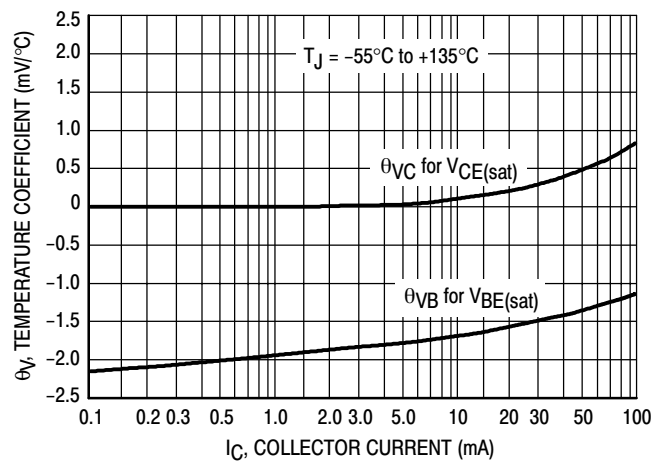
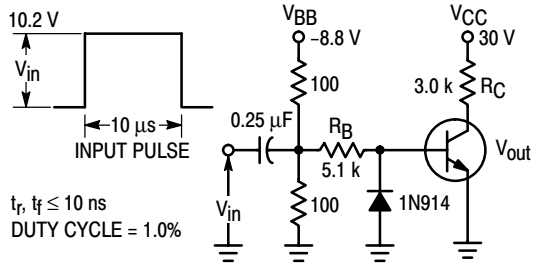


Figure 5. Temperature Coefficients

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Values Shown are for  $I_C @ 10 \text{ mA}$

Figure 6. Switching Time Test Circuit

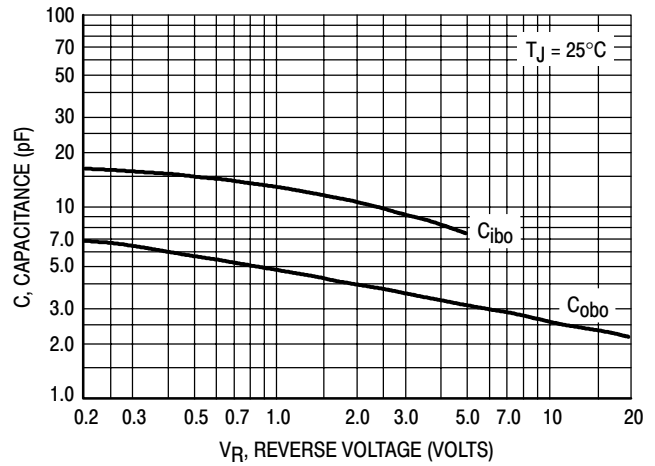


Figure 7. Capacitances

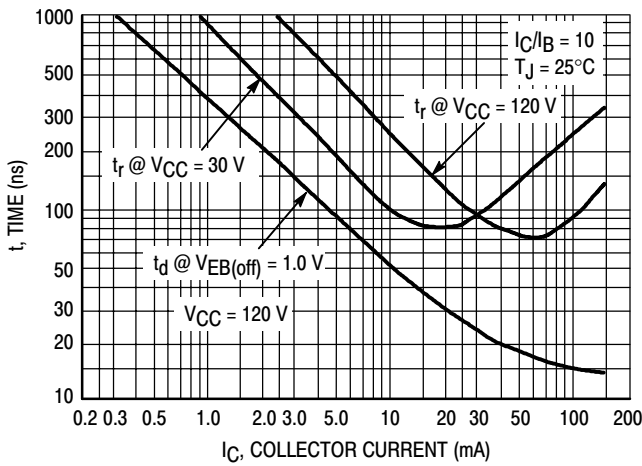


Figure 8. Turn-On Time

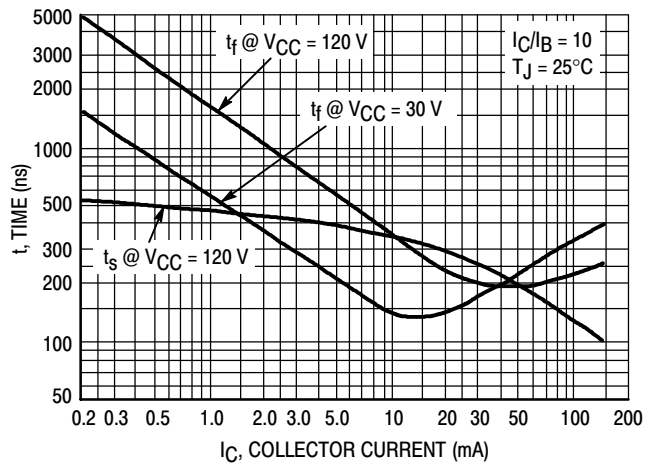
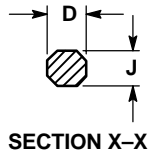
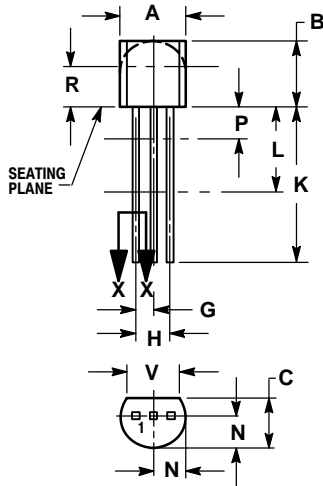


Figure 9. Turn-Off Time

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## PACKAGE DIMENSIONS

TO-92 (TO-226)  
CASE 29-11  
ISSUE AL



- YLE 1:  
PIN 1. EMITTER  
2. BASE  
3. COLLECTOR

### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---

**Notes**

**Notes**

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